

ABSTRACT

2D Material as Arsenene 3D Material as CsSbBr₃ Perovskite

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Two dimensional (2D) arsenene, a new allotropic form of arsenene with $\sqrt{3} \times \sqrt{3}$ $R30^\circ$ reconstruction, exhibiting electronic structure with metallic character, has been revealed on single crystal Ag(111) 1×1 at temperature of $\sim 450^\circ\text{C}$, whereas the 2D arsenene with 5×5 reconstruction, produces its appearance at a significantly lower temperature of $\sim 350^\circ\text{C}$. Interesting enough, it was discovered a reversible structural phase transition between these two surface reconstructions, under applying temperature, and/or electron gun irradiation, as established by Auger electron spectroscopy (AES), electron energy diffraction (LEED), and first-principle calculations, by using density functional theory, explicating both atomic structures and their associated band dispersions (ARPES) [1].

Furthermore, staying within the realm of 2D materials, the evidence of sp^2 -like hybridization of silicon valence orbitals in thin-and-thick Si grown on α -phase Si(111) $\sqrt{3} \times \sqrt{3}$ $R30^\circ$ Bi [2] was, recently, achieved. Instead, just 2D Si(111) islands, on β -phase Si(111) $\sqrt{3} \times \sqrt{3}$ $R30^\circ$ -Bi interface [3] were accomplished. However, moving towards extremely ordered 3D materials, the role of SiO₂ buffer layer in the molecular beam epitaxy growth of CsPbBr₃ perovskite on Si(111), will be also presented [4, 5].

[1] P. De Padova, C. Ottaviani, B. Olivieri and M. Krawiec, 2D Mater., 12 (2025) 025018.

[2] D. Garagnani, et al., Materials 2022, 15, 1730. <https://doi.org/10.3390/ma15051730>.

[3] P. De Padova, M. Jałochowski, A. Generosi, C. Ottaviani, C. Quaresima, B. Paci, B. Olivieri, M. Krawiec, Microstructure 2024;4:2024019, DOI:10.20517/microstructure.2023.74.

[4] P. De Padova, et al., Scientific Reports | (2024) 14:23618.

[5] C. Tantardini, et al., J. Phys. Chem. Lett. 2025, 16, 2385.